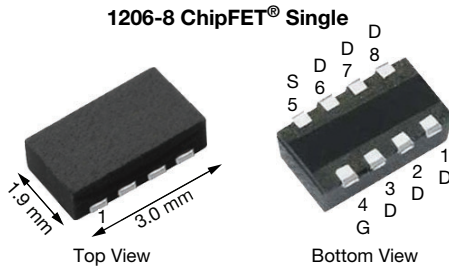




**THE DATASHEET OF
SI5475DDC-T1-GE3**



P-Channel 12 V (D-S) MOSFET



Marking code: BR

PRODUCT SUMMARY	
V_{DS} (V)	-12
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V	0.032
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5$ V	0.040
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8$ V	0.052
Q_g typ. (nC)	20
I_D (A) ^a	-6
Configuration	Single

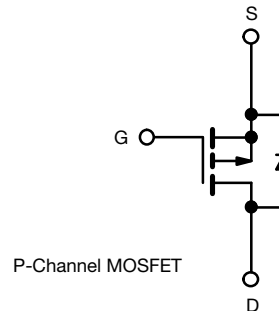
FEATURES

- TrenchFET[®] power MOSFET
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- Load switch for portable devices



ORDERING INFORMATION	
Package	1206-8 ChipFET
Lead (Pb)-free and halogen-free	Si5475DDC-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-12	V
Gate-source voltage	V_{GS}	± 8	
Continuous drain current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	-6 ^a
		$T_C = 70$ °C	-6 ^a
		$T_A = 25$ °C	-6 ^{a, b, c}
		$T_A = 70$ °C	-5.6 ^{b, c}
Pulsed drain current	I_{DM}	-20	A
Continuous source-drain diode current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	-1.9 ^{b, c}
Maximum power dissipation	P_D	$T_C = 25$ °C	5.7
		$T_C = 70$ °C	3
		$T_A = 25$ °C	2.3 ^{b, c}
		$T_A = 70$ °C	1.2 ^{b, c}
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient ^{b, f}	R_{thJA}	45	55	°C/W	
Maximum junction-to-foot (drain)	R_{thJF}	18	22		

Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 5$ s
- See solder profile (www.vishay.com/doc?73257). The 1206-8 ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 95 °C/W



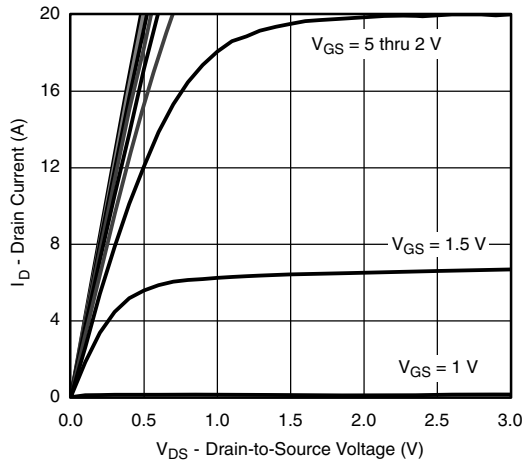
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-12	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-25	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	3	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-	-1	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V	-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = -12 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -12 V, V _{GS} = 0 V, T _J = 85 °C	-	-	-5	
On-state drain current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-20	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V, I _D = -5.4 A	-	0.026	0.032	Ω
		V _{GS} = -2.5 V, I _D = -4.8 A	-	0.032	0.040	
		V _{GS} = -1.8 V, I _D = -2 A	-	0.041	0.052	
Forward transconductance ^a	g _{fs}	V _{DS} = -6 V, I _D = -5.4 A	-	21	-	S
Dynamic ^b						
Input capacitance	C _{ISS}	V _{DS} = -6 V, V _{GS} = 0 V, f = 1 MHz	-	1600	-	pF
Output capacitance	C _{OSS}		-	400	-	
Reverse transfer capacitance	C _{RSS}		-	320	-	
Total gate charge	Q _g	V _{DS} = -6 V, V _{GS} = -8 V, I _D = -7.5 A	-	32	50	nC
		V _{DS} = -6 V, V _{GS} = -4.5 V, I _D = -7.5 A	-	20	30	
Gate-source charge	Q _{gs}		-	2.5	-	
Gate-drain charge	Q _{gd}		-	5.5	-	
Gate resistance	R _g	f = 1 MHz	-	4.1	-	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = -6 V, R _L = 1.1 Ω I _D ≅ -5.6 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	20	30	ns
Rise time	t _r		-	40	60	
Turn-off delay time	t _{d(off)}		-	45	70	
Fall time	t _f		-	20	30	
Turn-on delay time	t _{d(on)}	V _{DD} = -6 V, R _L = -1.1 Ω I _D ≅ -5.6 A, V _{GEN} = -8 V, R _g = 1 Ω	-	10	15	
Rise time	t _r		-	12	20	
Turn-off delay time	t _{d(off)}		-	45	70	
Fall time	t _f		-	15	25	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	-4.8	A
Pulse diode forward current	I _{SM}		-	-	-20	
Body diode voltage	V _{SD}	I _S = -5.6 A, V _{GS} = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t _{rr}	I _F = -5.6 A, di/dt = 100 A/μs, T _J = 25 °C	-	42	65	ns
Body diode reverse recovery charge	Q _{rr}		-	50	75	nC
Reverse recovery fall time	t _a		-	20	-	ns
Reverse recovery rise time	t _b		-	22	-	

Notes

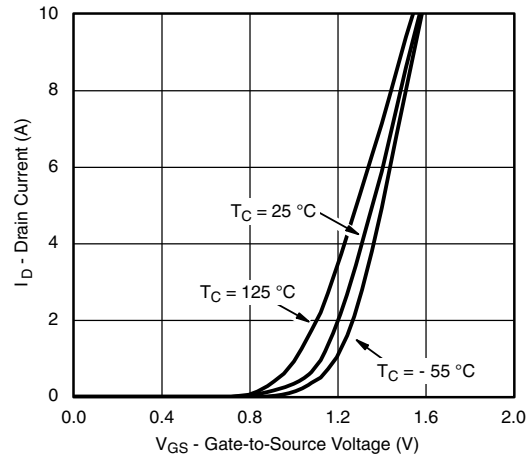
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

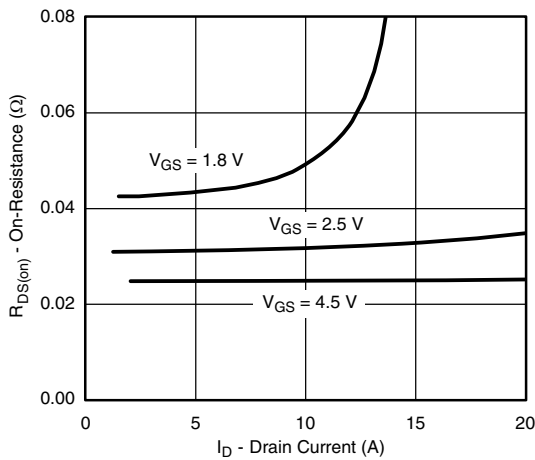
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



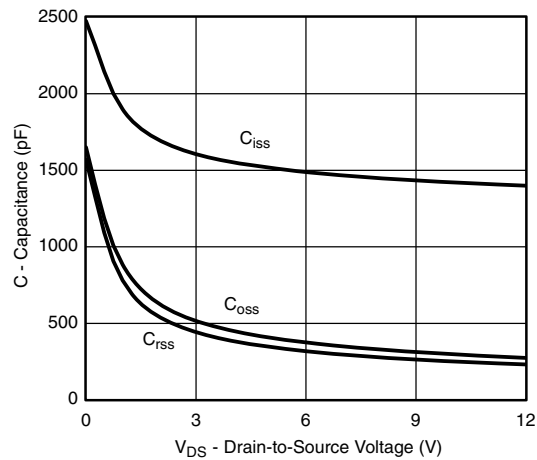
Output Characteristics



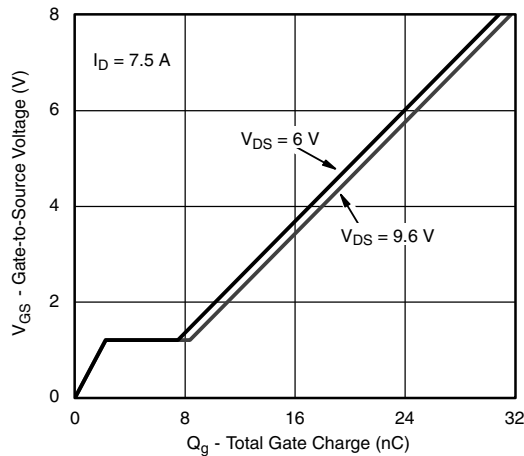
Transfer Characteristics



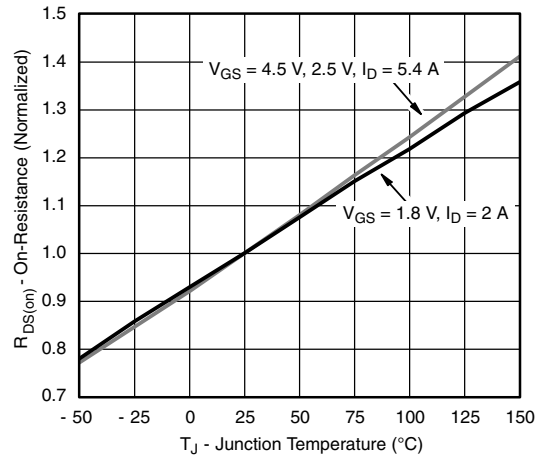
On Resistance vs. Drain Current



Capacitance



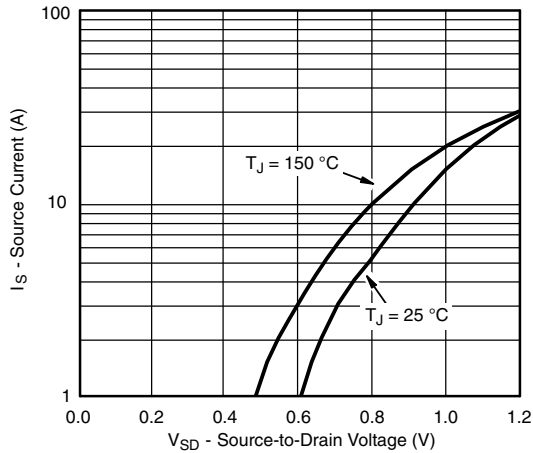
Gate Charge



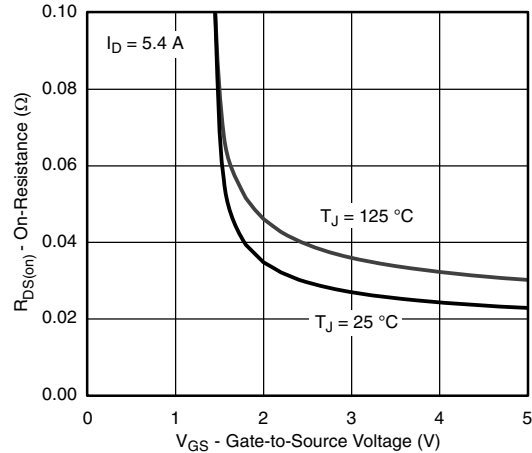
On-Resistance vs. Junction Temperature



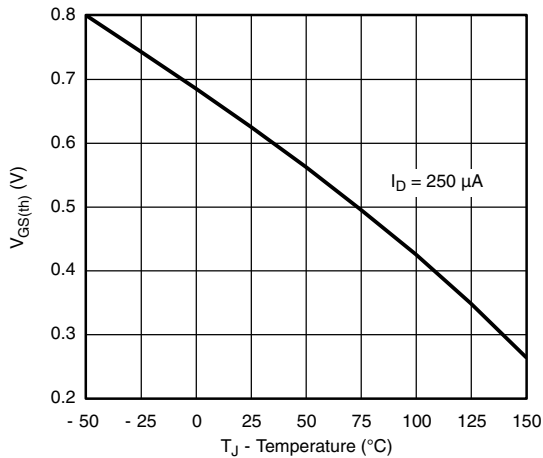
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



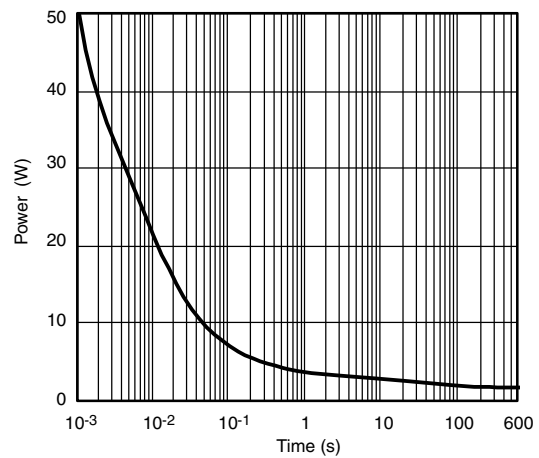
Forward Diode Voltage vs. Temperature



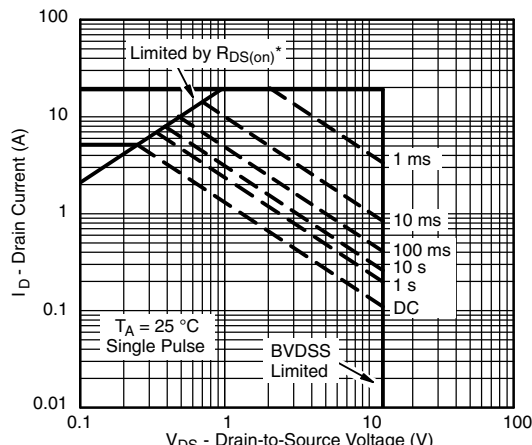
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



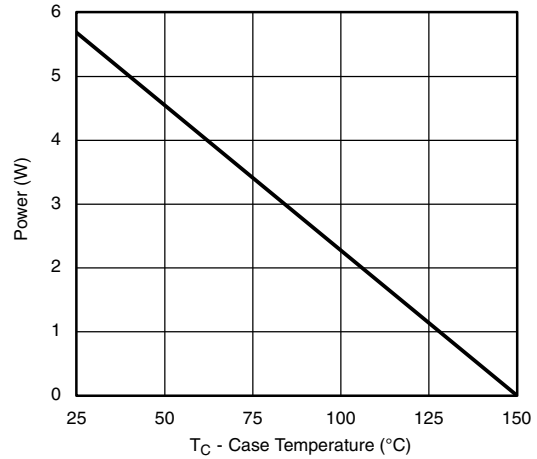
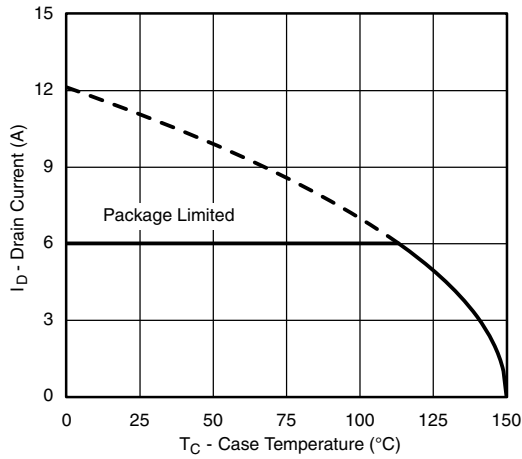
Single Pulse Power



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

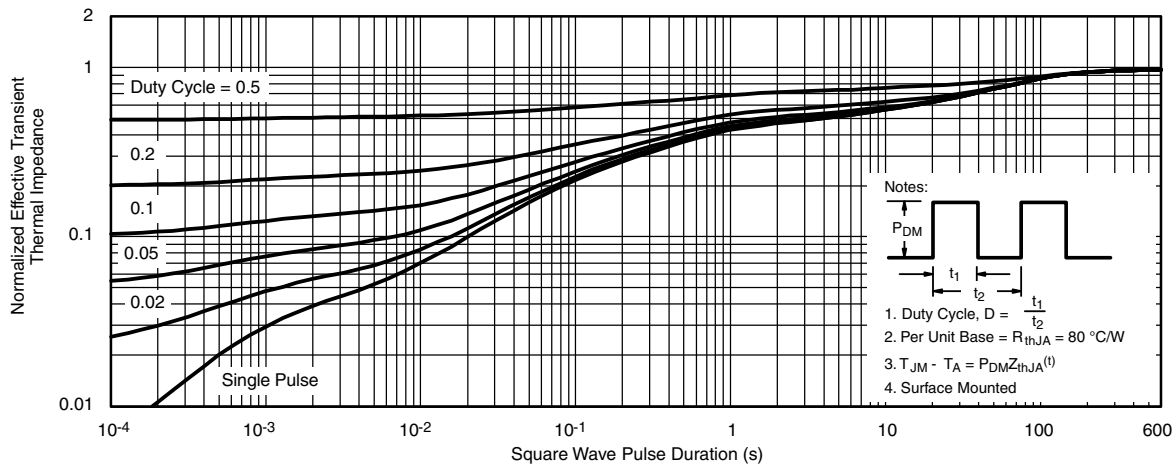


Note

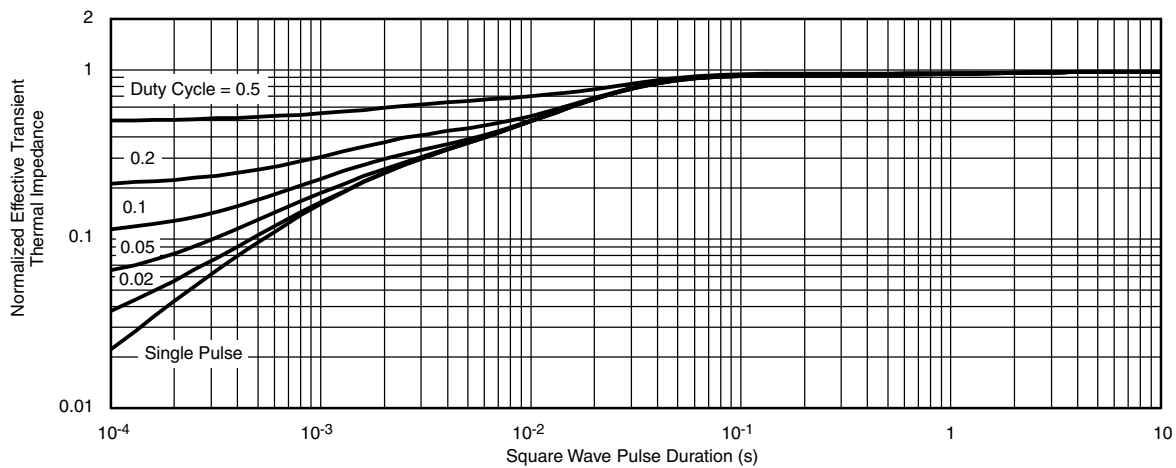
- a. The power dissipation P_D is based on $T_J \text{ max.} = 150 \text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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